Photoconductive Series

Planar Diffused Silicon Photodiodes

The Photoconductive Detector Series are suitable for high speed and high sensitivity applications. The spectral range extends from 350 to 1100 nm, making these photodiodes ideal for visible and near IR applications, including such AC applications as detection of pulsed LASER sources, LEDs, or chopped light.

To achieve high speeds, these detectors should be reverse biased. Typical response times from 10 ns to 250 ns can be achieved with a 10V reverse bias, for example. When a reverse bias is applied, capacitance decreases (as seen in the figure below) corresponding directly to an increase in speed.

As indicated in the specification table, the reverse bias should not exceed 30 volts. Higher bias voltages will result in permanent damage to the detector.

Since a reverse bias generates additional dark current, the noise in the device will also increase with applied bias. For lower noise detectors, the Photovoltaic Series should be considered.

Refer to the Photoconductive Mode (PC) paragraph in the "Photodiode Characteristics" section of this catalog for detailed information on electronics set up.

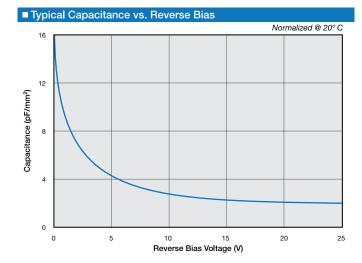


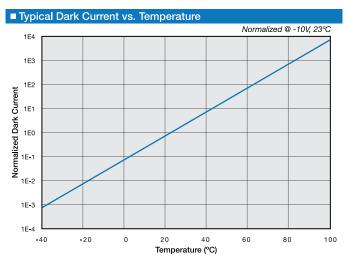
APPLICATIONS

- Pulse Detectors
- Optical Communications
- Bar Code Readers
- Optical Remote Control
- Medical Equipment
- High Speed Photometry

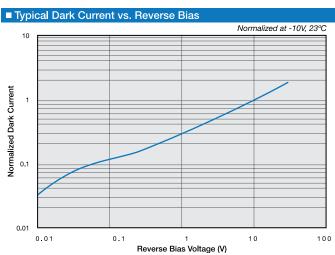
FEATURES

- High Speed Response
- Low Capacitance
- Low Dark Current
- Wide Dynamic Range
- High Responsivity









■ Photoconductive Series

Typical Electro-Optical Specifications at T_A=23°C

Model Number	Active Area		Peak Responsivity Wavelength	Responsivity at λp		Capacitance (pF)		Dark Current (nA)		NEP (W/√Hz)	Reverse Voltage	Rise Time (ns)	Ten Rai (°	nge	
	Area (mm²)	Dimensions (mm)	λp (nm)	(A/W)		ov	-10 V	-10 V		-10V 970nm	(V)	-10V 632nm 50 Ω	Operating	Storage	Package Style ¶
			typ.	min.	typ.	typ.	typ.	typ.	max.	typ.	max.	typ.	obe	St	
'D' Series, Metal Package															
PIN-020A	0.20	0.51 φ		0.60	0.65	4	1	0.01	0.15	2.8 e-15	6 8 10 12 30 14 17 24 43 250	6			1 / TO 10
PIN-040A	0.81	1.02 φ				8	2	0.05	0.50	6.2 e-15		8			1 / TO-18
PIN-2DI ‡	1.1	0.81 x 1.37				25	5	0.10	1.0	8.7 e-15		10			4 / TO-18
PIN-3CDI PIN-3CD	3.2	1.27 x 2.54	970			45	12	0.15	2	1.1 e-14		10			7 / TO-18
PIN-5DI PIN-5D	5.1	2.54 φ				85	15	0.25	3	1.4 e-14		12	~ +100	~ +125	2 / TO-5 5 / TO-5
PIN-13DI	13	3.6 sq				225	40	0.35	6	1.6 e-14		14	-40	-55	2 / TO-5
PIN-13D PIN-6DI	16.4	4.57 φ				330	60	0.5	10	1.9 e-14		17			5 / TO-5 3 / TO-8
PIN-6D PIN-44DI	10.4	4.57 φ				330	60	0.5	10	1.9 e-14		17			6 / TO-8 3 / TO-8
PIN-44D	44	6.6 sq				700	130	1	15	2.8 e-14		24			6 / TO-8
PIN-10DI PIN-10D	100	11.28 ф				1500	300	2	25	3.9 e-14		43	-10 ~ +60	~ +70	10/ Lo-Prof 11 / BNC
PIN-25D	613	27.9 ф				9500	1800	15	1000	1.1 e-13		250		-20	12 / BNC
`O' Series, Metal Package															
OSD1-0	1	1.0 sq		0.47	0.54	12	3	1	3	4.5 e-14	50	10	5	-40 ~ +100	7 / TO-18
OSD5-0	5	2.5 φ				50	8	5	10	1.0 e-13		8			5 / TO-5
OSD15-0	15	3.8 sq	900			150	20	8	15	1.3 e-13		9	, +75		5 / TO-5
OSD35-0	35	5.9 sq	900			350	46	12	30	1.6 e-13		12	-25 ~		3 / TO-8
OSD60-0	58	7.6 sq				600	75	15	50	1.7 e-13		14		4	72/ TO-8
OSD100-0A	100	11.3 ф				1000	130	30	70	2.5 e-13		19			74 /Special
`D' Serie	es, Pl	astic F	Packag	je §											
FIL-5C	5.1	2.54 φ	970	0.60	0.65	85	15	0.25	3	1.4 e-14	30	12	-10 ~ +60	-20 ~ +70	14 / 51
FIL-20C	16.4	4.57 φ				330	60	0.5	10	1.9 e-14		17			14 / Plastic
FIL-44C	44	6.6 sq				700	130	1	15	2.8 e-14		24			1E / DI .:
FIL-100C	100	11.28 ф				1500	300	2	25	3.9 e-14		43			15 / Plastic
PIN-220D	200	10 x 20				3200	600	5	100	6.2 e-14		75			27 / Plastic

[‡] The 'l' suffix on the model number is indicative of the photodiode chip being isolated from the package by an additional pin connected to the case. § The photodiode chips in "FIL" series are isolated in a low profile plastic package. They have a large field of view as well as "in line" pins.
¶ For mechanical drawings please refer to pages 58 thru 69.
* Non-condensing temperature and storage range, Non-condensing environment.

1. Parameter Definitions:

- A = Distance from top of chip to top of glass.
- a = Photodiode Anode.
- B = Distance from top of glass to bottom of case.
- c = Photodiode Cathode
- (Note: cathode is common to case in metal package products unless otherwise noted).
- W = Window Diameter.
- F.O.V. = Filed of View (see definition below).
- 2. Dimensions are in inches (1 inch = 25.4 mm).
- 3. Pin diameters are 0.018 ± 0.002" unless otherwise specified.
- 4. Tolerances (unless otherwise noted)

General: 0.XX ±0.01"

0.XXX ±0.005"

Chip Centering: ±0.010" Dimension 'A': ±0.015"

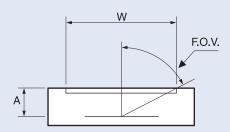
5. Windows

All '**UV**' Enhanced products are provided with QUARTZ glass windows, 0.027 ± 0.002 " thick.

All 'XUV' products are provided with removable windows.

All 'DLS' PSD products are provided with A/R coated glass windows.

All 'FIL' photoconductive and photovoltaic products are epoxy filled instead of glass windows.



$$F.O.V. = \tan^{-1} \left(\frac{W}{2A}\right)$$



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